

650V N-Channel MOSFET

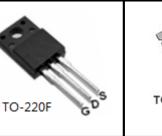
FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

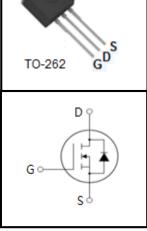
APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information				
Device	Package	Marking		
CS7N65F	TO-220F	CS7N65F		
CS7N65P	TO-220	CS7N65P		
CS7N65K	TO-262	CS7N65K		







Absolute Maximum Ratings $T_c = 25^{\circ}C$, unless otherwise noted							
Decementer		Cumhal	Value			Unit	
Parameter		Symbol	TO-220F	TO-262	TO-220	- Unit	
Drain-Source Voltage ($V_{GS} = 0V$)		V _{DSS}		650		V	
Continuous Drain Current		I _D		7		A	
Pulsed Drain Current	(note1)	I _{DM}	28			A	
Gate-Source Voltage		V_{GSS}		±30		V	
Single Pulse Avalanche Energy	(note2)	E _{AS}	165		mJ		
Avalanche Current	(note1)	I _{AS}	5.76		А		
Repetitive Avalanche Energy	(note1)	E _{AR}	100		mJ		
Power Dissipation (T _C = 25°C)		P _D	63	97		W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55~+150		°C		

Thermal Resistance					
Deservation	Symbol	Value			
Parameter		TO-220F	TO-262	TO-220	Unit
Thermal Resistance, Junction-to-Case	R _{thJC}	1.98	1.29		K/W
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62.5	60		



Specifications $T_J = 25^{\circ}C$, unless otherwise noted								
Parameter	Symbol	Test Conditions	Value			Unit		
	Symbol	rest conditions	Min.	Тур.	Max.	Unit		
Static				_				
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_{D} = 250 \mu A$	650			V		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 650V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA		
Gate-Source Leakage	I _{GSS}	V_{GS} = $\pm 30V$			±100	nA		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3.0		4.0	V		
Drain-Source On-Resistance (Note3)	R _{DS(on)}	$V_{GS} = 10V, I_{D} = 3.5A$		1.1	1.35	Ω		
Dynamic								
Input Capacitance	C _{iss}	$\mathcal{M} = \mathcal{O}\mathcal{M}$		891		pF		
Output Capacitance	C _{oss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$		87				
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		10				
Total Gate Charge	Q _g			32		nC		
Gate-Source Charge	Q _{gs}	$V_{DD} = 520V, I_{D} = 7A, V_{GS} = 10V$		4.6				
Gate-Drain Charge	Q_{gd}			14				
Turn-on Delay Time	t _{d(on)}			39				
Turn-on Rise Time	t _r	V _{DD} = 325V, I _D = 7A,		23		ns		
Turn-off Delay Time	t _{d(off)}	$R_{G} = 25 \Omega$		137				
Turn-off Fall Time	t _f			30				
Drain-Source Body Diode Character	istics							
Continuous Body Diode Current	۱ _s	T 05.00			7.0	A		
Pulsed Diode Forward Current	I _{SM}	T _C = 25 °C			28			
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 3.5A, V _{GS} = 0V			1.4	V		
Reverse Recovery Time	t _{rr}	V _{GS} = 0V,I _S = 7A,		575		ns		
Reverse Recovery Charge	Q _{rr}	di _F /dt =100A /µs		1.9		μC		

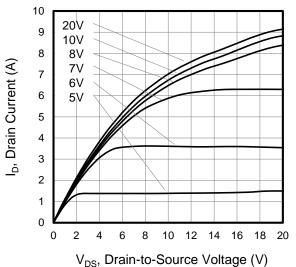
Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25 °C
- 3. Pulse Test: Pulse width \leq 300µs, Duty Cycle \leq 1%



Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

Figure 1. Output Characteristics (T_J = 25°C)





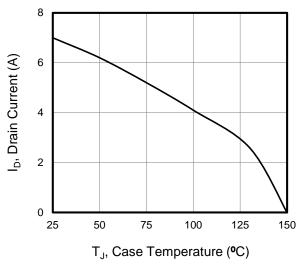
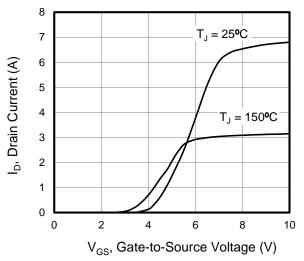


Figure 5. Transfer Characteristics



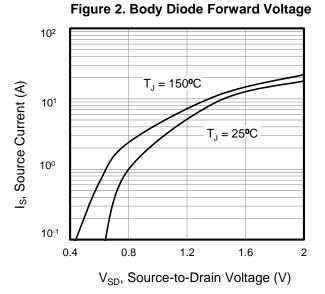


Figure 4. BV_{DSS} Variation vs. Temperature

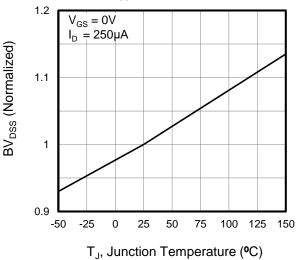
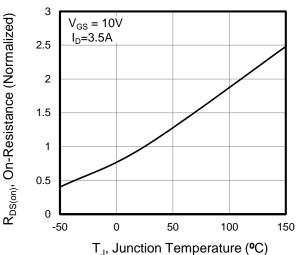
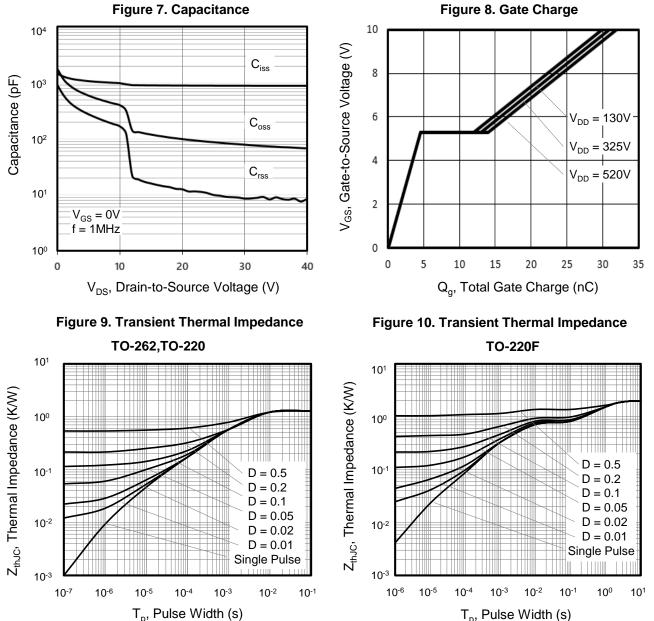


Figure 6. On-Resistance vs. Temperature





Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted



T_p, Pulse Width (s)



Figure A: Gate Charge Test Circuit and Waveform

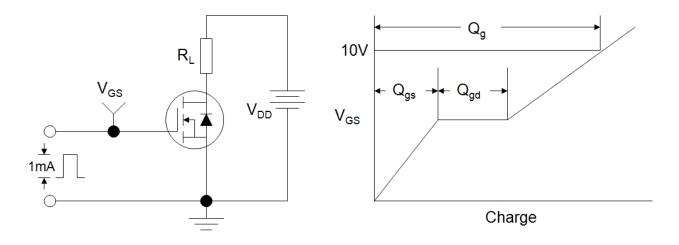


Figure B: Resistive Switching Test Circuit and Waveform

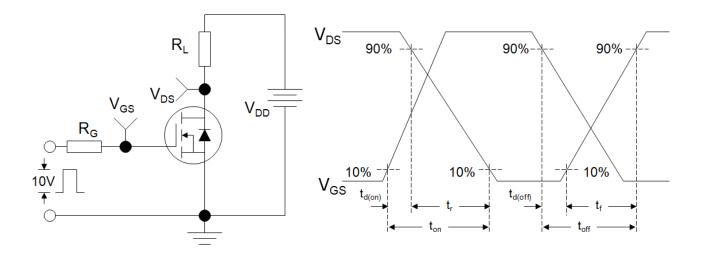
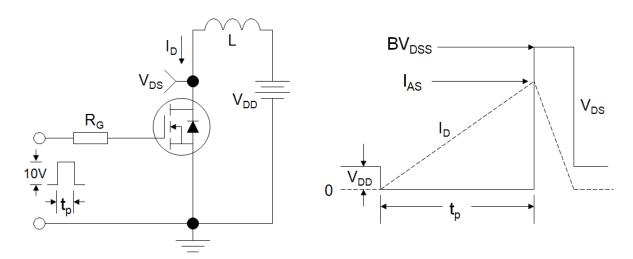
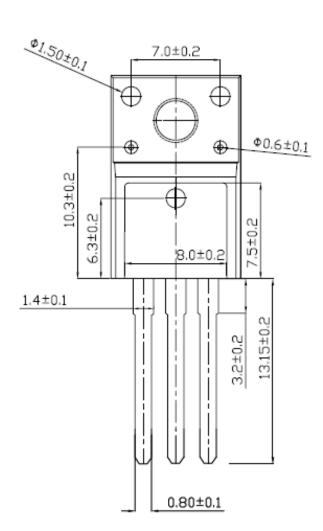


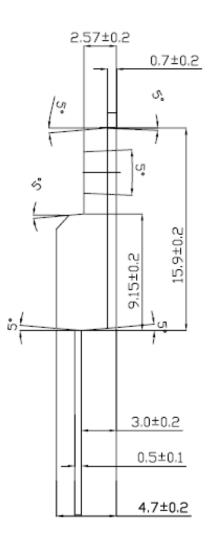
Figure C: Unclamped Inductive Switching Test Circuit and Waveform





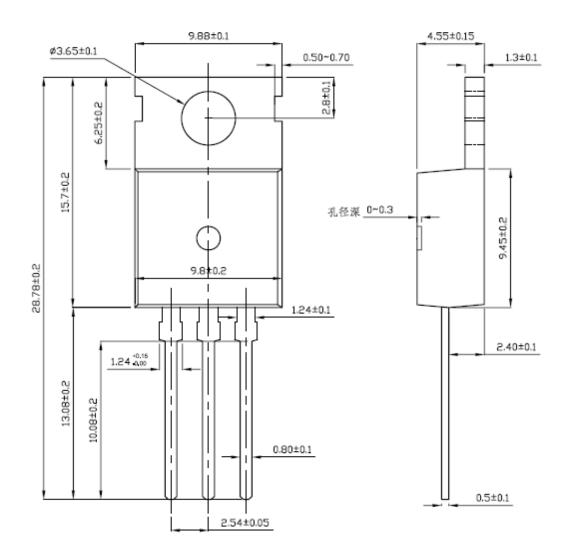
TO-220F





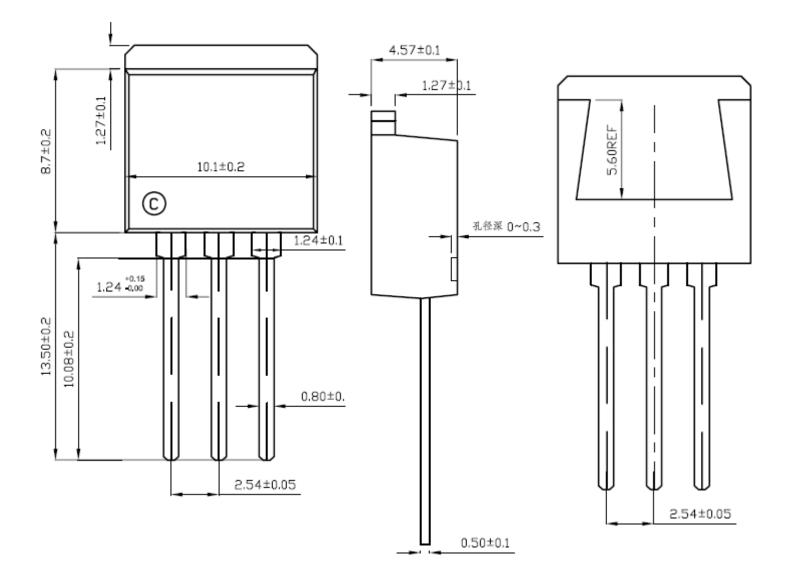


TO-220





TO-262





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